## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims**:

- 1. (Original) A dicing and die bonding pressure-sensitive adhesive sheet comprising a base material and a pressure-sensitive adhesive layer disposed thereon, the pressure-sensitive adhesive layer having a ratio  $(M_{100}/M_{70})$  of a modulus of elasticity at  $100^{\circ}$ C  $(M_{100})$  to a modulus of elasticity at  $70^{\circ}$ C  $(M_{70})$  being 0.5 or less.
- 2. (Original) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 1, wherein the pressure-sensitive adhesive layer comprises a pressure-sensitive component and a thermosetting component, the pressure-sensitive component comprising an acrylic polymer having a weight-average molecular weight of 30,000 to 500,000.
- 3. (Original) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 2, wherein the acrylic polymer contains repeating units derived from vinyl acetate in an amount of 5 to 50% by mass.
- 4. (Currently Amended) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 2—or 3, wherein the pressure-sensitive adhesive layer further contains a thermoplastic resin having a glass transition temperature of 60 to 150°C.
- 5. (Original) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 4, wherein the weight ratio of the acrylic polymer and the thermoplastic resin (acrylic polymer/thermoplastic resin) ranges from 9/1 to 3/7.
- 6. (Currently Amended) The dicing and die bonding pressure-sensitive adhesive sheet according to any one of claims 1 to 5claim 1, wherein the base material has a

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surface tension of 40 mN/m or less at a surface which contacts with the pressure-sensitive adhesive layer.

- 7. (Currently Amended) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in any one of claims 1 to 6 claim 1, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.
- 8. (New) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 3, wherein the pressure-sensitive adhesive layer further contains a thermoplastic resin having a glass transition temperature of 60 to 150°C.
- 9. (New) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 2, wherein the base material has a surface tension of 40 mN/m or less at a surface which contacts with the pressure-sensitive adhesive layer.
- 10. (New) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 3, wherein the base material has a surface tension of 40 mN/m or less at a surface which contacts with the pressure-sensitive adhesive layer.
- 11. (New) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 4, wherein the base material has a surface tension of 40 mN/m or less at a surface which contacts with the pressure-sensitive adhesive layer.
- 12. (New) The dicing and die bonding pressure-sensitive adhesive sheet according to claim 5, wherein the base material has a surface tension of 40 mN/m or less at a surface which contacts with the pressure-sensitive adhesive layer.

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- 13. (New) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in claim 2, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.
- 14. (New) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in claim 3, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.
- 15. (New) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in claim 4, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.
- 16. (New) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in claim 5, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.

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17. (New) A process for producing semiconductor devices, the process comprising sticking a semiconductor wafer onto the pressure-sensitive adhesive layer of the dicing and die bonding pressure-sensitive adhesive sheet as claimed in claim 6, dicing the semiconductor wafer into IC chips, picking up the IC chips from the base material while allowing the pressure-sensitive adhesive layer to remain adhered to the IC chips, and bonding the IC chips onto die pads by means of the pressure-sensitive adhesive layer with the application of heat and pressure.